

$V_{DRM} = 7200 \text{ V}$
 $I_{T(AV)M} = 5040 \text{ A}$
 $I_{T(RMS)} = 7910 \text{ A}$
 $I_{TSM} = 92.0 \cdot 10^3 \text{ A}$
 $V_{T0} = 0.983 \text{ V}$
 $r_T = 0.128 \text{ m}\Omega$

Phase Control Thyristor

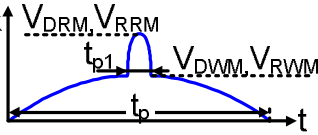
5STP 48Y7200

Doc. No. 5SYA1076-05 Mar. 21

- Patented free-floating silicon technology
- Low on-state and switching losses
- Designed for traction, energy and industrial applications
- Optimum power handling capability
- Interdigitated amplifying gate
- Custom irradiation variant available on request

Blocking

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	5STP 48Y7200	Unit
Max. surge peak forward and reverse blocking voltage	V_{DSM} , V_{RSM}	$t_p = 10 \text{ ms}$, $f = 5 \text{ Hz}$ $T_{vj} = 5 \dots 110 \text{ }^\circ\text{C}$, Note 1	7200	V
Max repetitive peak forward and reverse blocking voltage	V_{DRM} , V_{RRM}	$f = 50 \text{ Hz}$, $t_p = 10 \text{ ms}$, $t_{p1} = 250 \text{ }\mu\text{s}$, $T_{vj} = 5 \dots 110 \text{ }^\circ\text{C}$, Note 1, Note 2	7200	V
Max crest working forward and reverse voltages	V_{DWM} , V_{RWM}		4800	V
Critical rate of rise of commutating voltage	dv/dt_{crit}	Exp. to $0.67 \cdot V_{DRM}$, $T_{vj} = 110 \text{ }^\circ\text{C}$	2000	V/ μs

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward leakage current	I_{DRM}	V_{DRM} , $T_{vj} = 110 \text{ }^\circ\text{C}$			2000	mA
Reverse leakage current	I_{RRM}	V_{RRM} , $T_{vj} = 110 \text{ }^\circ\text{C}$			2000	mA

Note 1: Voltage de-rating factor of 0.11% per $^\circ\text{C}$ is applicable for T_{vj} below $+5 \text{ }^\circ\text{C}$.

Note 2: Recommended minimum ratio of V_{DRM} / V_{DWM} or $V_{RRM} / V_{RWM} = 2$. See App. Note 5SYA 2051.

Mechanical data

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Mounting force	F_M		170	190	210	kN
Acceleration	a	Device unclamped			50	m/s^2
Acceleration	a	Device clamped			100	m/s^2

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Weight	m				5.14	kg
Housing thickness	H	$F_M = 190 \text{ kN}$, $T_a = 25 \text{ }^\circ\text{C}$	34.74		35.19	mm
Surface creepage distance	D_s		56			mm
Air strike distance	D_a		22			mm

1) Maximum rated values indicate limits beyond which damage to the device may occur

On-state**Maximum rated values ¹⁾**

Parameter	Symbol	Conditions	min	typ	max	Unit
Average on-state current	$I_{T(AV)M}$	Half sine wave, $T_c = 70\text{ °C}$			5040	A
RMS on-state current	$I_{T(RMS)}$				7910	A
Peak non-repetitive surge current	I_{TSM}	$t_p = 10\text{ ms}$, $T_{vj} = 110\text{ °C}$, sine half wave,			$92.0 \cdot 10^3$	A
Limiting load integral	I^2t	$V_D = V_R = 0\text{ V}$, after surge			$42.3 \cdot 10^6$	A^2s
Peak non-repetitive surge current	I_{TSM}	$t_p = 10\text{ ms}$, $T_{vj} = 110\text{ °C}$, sine half wave,			$75.4 \cdot 10^3$	A
Limiting load integral	I^2t	$V_R = 0.6 \cdot V_{RRM}$, after surge			$28.4 \cdot 10^6$	A^2s

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
On-state voltage	V_T	$I_T = 6000\text{ A}$, $T_{vj} = 110\text{ °C}$		1.68	1.75	V
Threshold voltage	$V_{(T0)}$	$I_T = 3000\text{ A} - 6000\text{ A}$, $T_{vj} = 110\text{ °C}$		0.969	0.983	V
Slope resistance	r_T				0.118	0.128
Holding current	I_H	$T_{vj} = 25\text{ °C}$			150	mA
		$T_{vj} = 110\text{ °C}$			100	mA
Latching current	I_L	$T_{vj} = 25\text{ °C}$			1500	mA
		$T_{vj} = 110\text{ °C}$			1000	mA

Switching**Maximum rated values ¹⁾**

Parameter	Symbol	Conditions	min	typ	max	Unit
Critical rate of rise of on-state current	di/dt_{crit}	$T_{vj} = 110\text{ °C}$ $V_D \leq 0.67 \cdot V_{DRM}$ $I_{GM} = 5\text{ A}$ $t_r = 0.5\text{ }\mu s$			200	$A/\mu s$
		Cont. $f = 50\text{ Hz}$ $I_T = 3000\text{ A}$				
Circuit-commutated turn-off time	t_q	$T_{vj} = 110\text{ °C}$, $I_T = 3000\text{ A}$ $V_R = 200\text{ V}$, $di_T/dt = -1.5\text{ A}/\mu s$ $V_D \leq 0.67 \cdot V_{DRM}$, $dV_D/dt = 20\text{ V}/\mu s$			700	μs
		Cont. $f = 1\text{ Hz}$ $I_T = 2000\text{ A}$				

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Reverse recovery charge	Q_{rr}	$T_{vj} = 110\text{ °C}$, $I_T = 3000\text{ A}$, $V_R = 200\text{ V}$, $di_T/dt = -1.5\text{ A}/\mu s$		6940	7900	μAs
Reverse recovery current	I_{RM}		60	91	140	A
Gate turn-on delay time	t_{gd}	$T_{vj} = 25\text{ °C}$, $V_D = 0.4 \cdot V_{RM}$, $I_{GM} = 5\text{ A}$, $t_r = 0.5\text{ }\mu s$	1		3	μs

Triggering

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Peak forward gate voltage	V _{FGM}				12	V
Peak forward gate current	I _{FGM}				10	A
Peak reverse gate voltage	V _{RGM}				10	V
Average gate power loss	P _{G(AV)}		see Fig. 7			W

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Gate-trigger voltage	V _{GT}	T _{vj} = 25 °C			2.6	V
Gate-trigger current	I _{GT}	T _{vj} = 25 °C			400	mA
Gate non-trigger voltage	V _{GD}	V _D = 0.4·V _{DRM} , T _{vjmax} = 110 °C			0.3	V
Gate non-trigger current	I _{GD}	V _D = 0.4·V _{DRM} , T _{vjmax} = 110 °C			10	mA

Thermal

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Operating junction temperature range	T _{vj}		5		110	°C
Storage temperature range	T _{stg}		-40		140	°C

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Thermal resistance junction to case	R _{th(j-c)}	Double-side cooled F _m = 170... 210 kN			3	K/kW
	R _{th(j-c)A}	Anode-side cooled F _m = 170... 210 kN			6	K/kW
	R _{th(j-c)C}	Cathode-side cooled F _m = 170... 210 kN			6	K/kW
Thermal resistance case to heatsink	R _{th(c-h)}	Double-side cooled F _m = 170... 210 kN			0.6	K/kW
	R _{th(c-h)}	Single-side cooled F _m = 170... 210 kN			1.2	K/kW

Analytical function for transient thermal impedance:

$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i (1 - e^{-t/\tau_i})$$

i	1	2	3	4
R _i (K/kW)	1.986	0.608	0.267	0.138
τ _i (s)	0.9238	0.1372	0.0188	0.0047

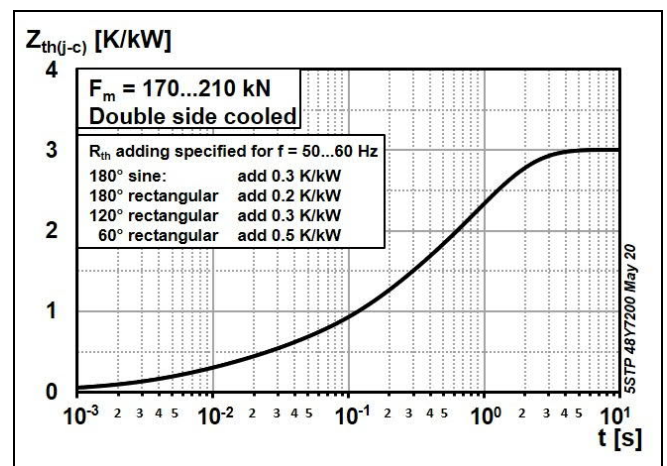


Fig. 1 Transient thermal impedance (junction-to-case) vs. time

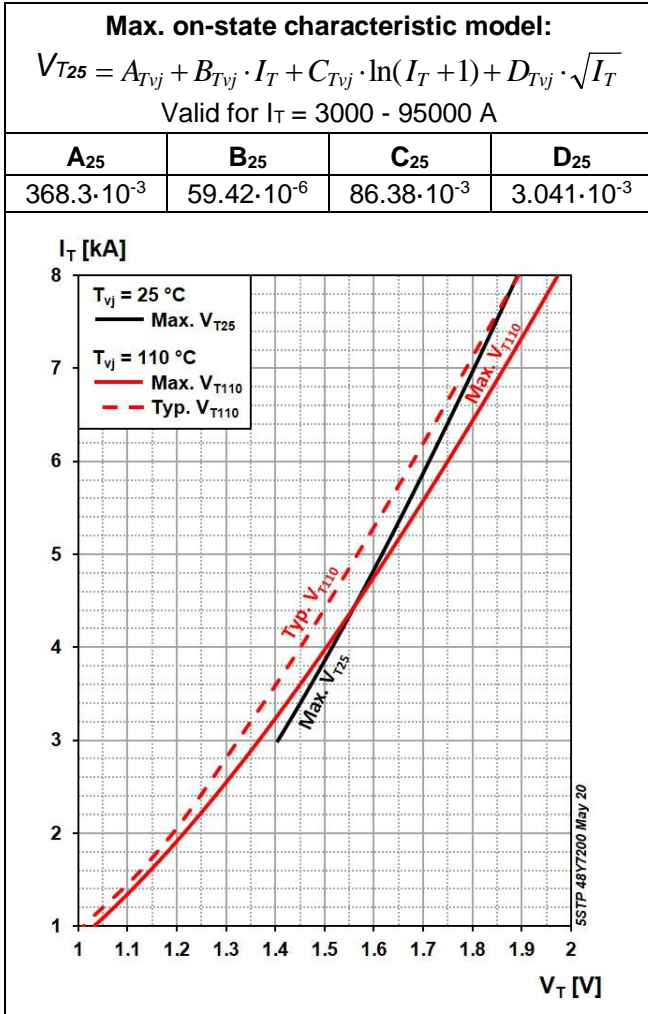


Fig. 2 On-state voltage characteristics

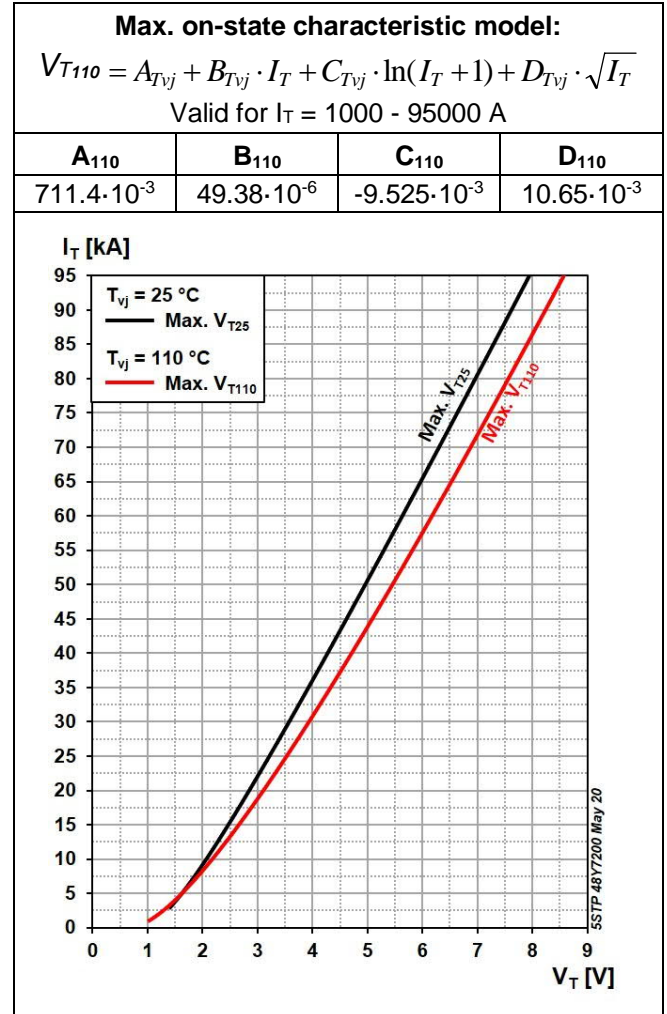


Fig. 3 On-state voltage characteristics

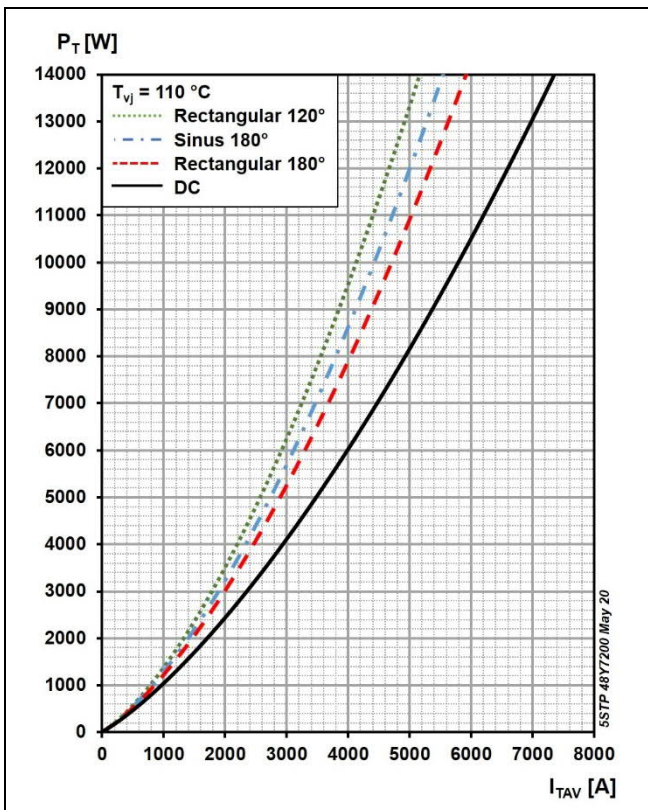


Fig. 4 On-state power dissipation vs. mean on-state current, turn-on losses excluded

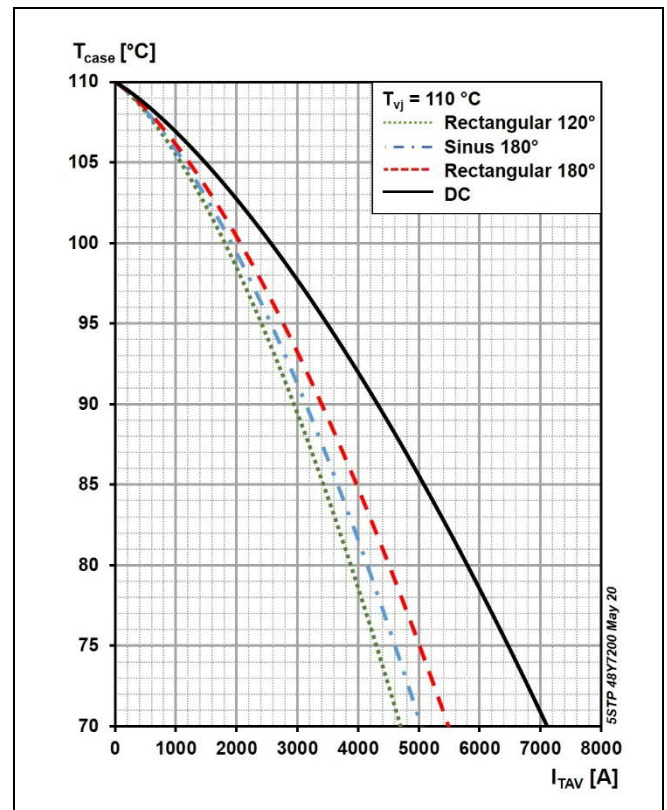


Fig. 5 Max. permissible case temperature vs. mean on-state current, switching losses ignored

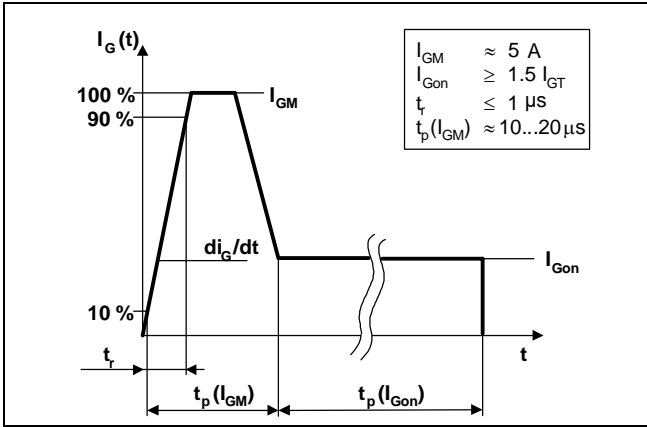


Fig. 6 Recommended gate current waveform

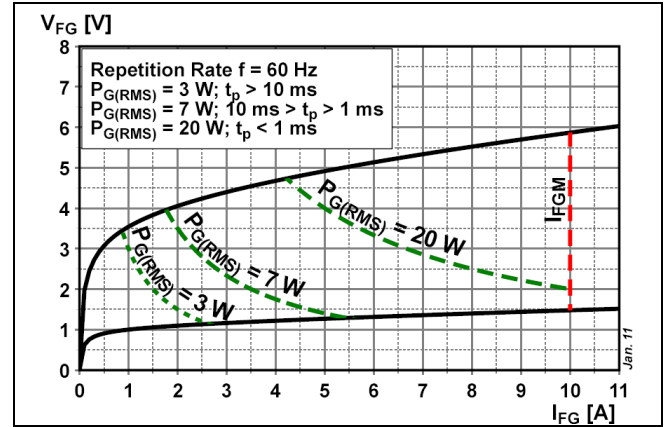


Fig. 7 Max. peak gate power loss

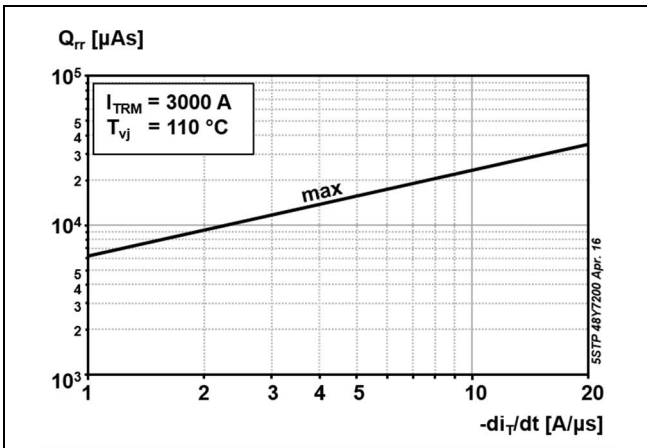


Fig. 8 Reverse recovery charge vs. decay rate of on-state current

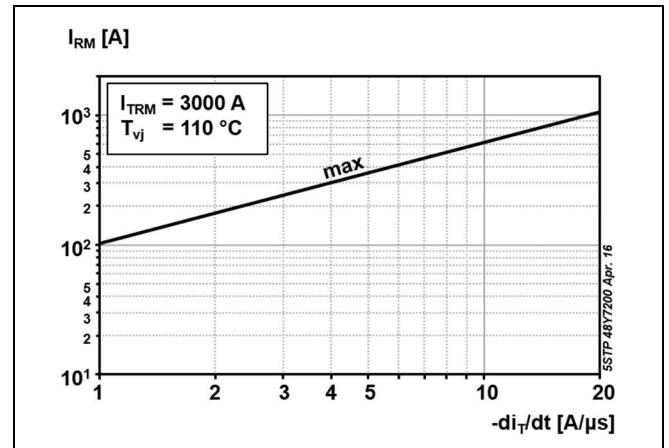


Fig. 9 Peak reverse recovery current vs. decay rate of on-state current

Power losses

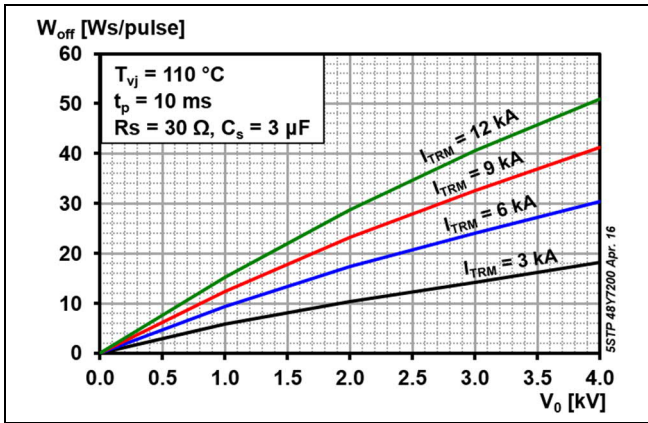


Fig. 10 Turn-off energy, half sinusoidal waves

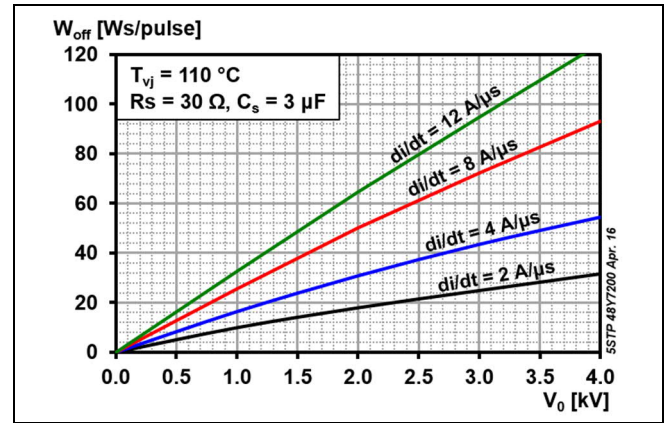


Fig. 11 Turn-off energy, rectangular waves

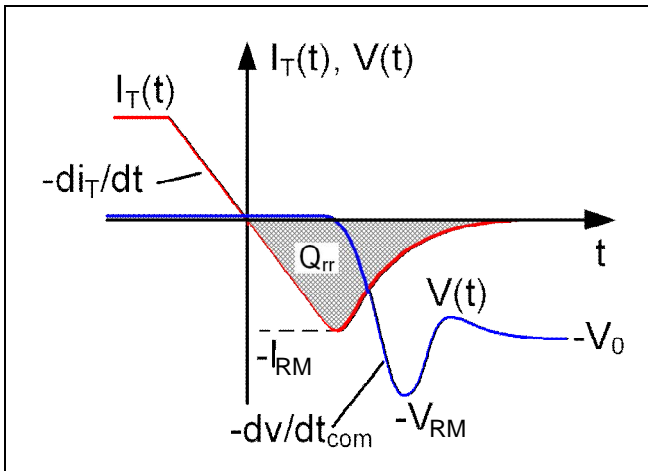


Fig. 12 Current and voltage waveforms at turn-off

Total power loss for repetitive waveforms:

$$P_{TOT} = P_T + W_{on} \cdot f + W_{off} \cdot f$$

where

$$P_T = \frac{1}{T} \int_0^T I_T \cdot V_T(I_T) dt$$

Fig. 13 Relationships for power loss

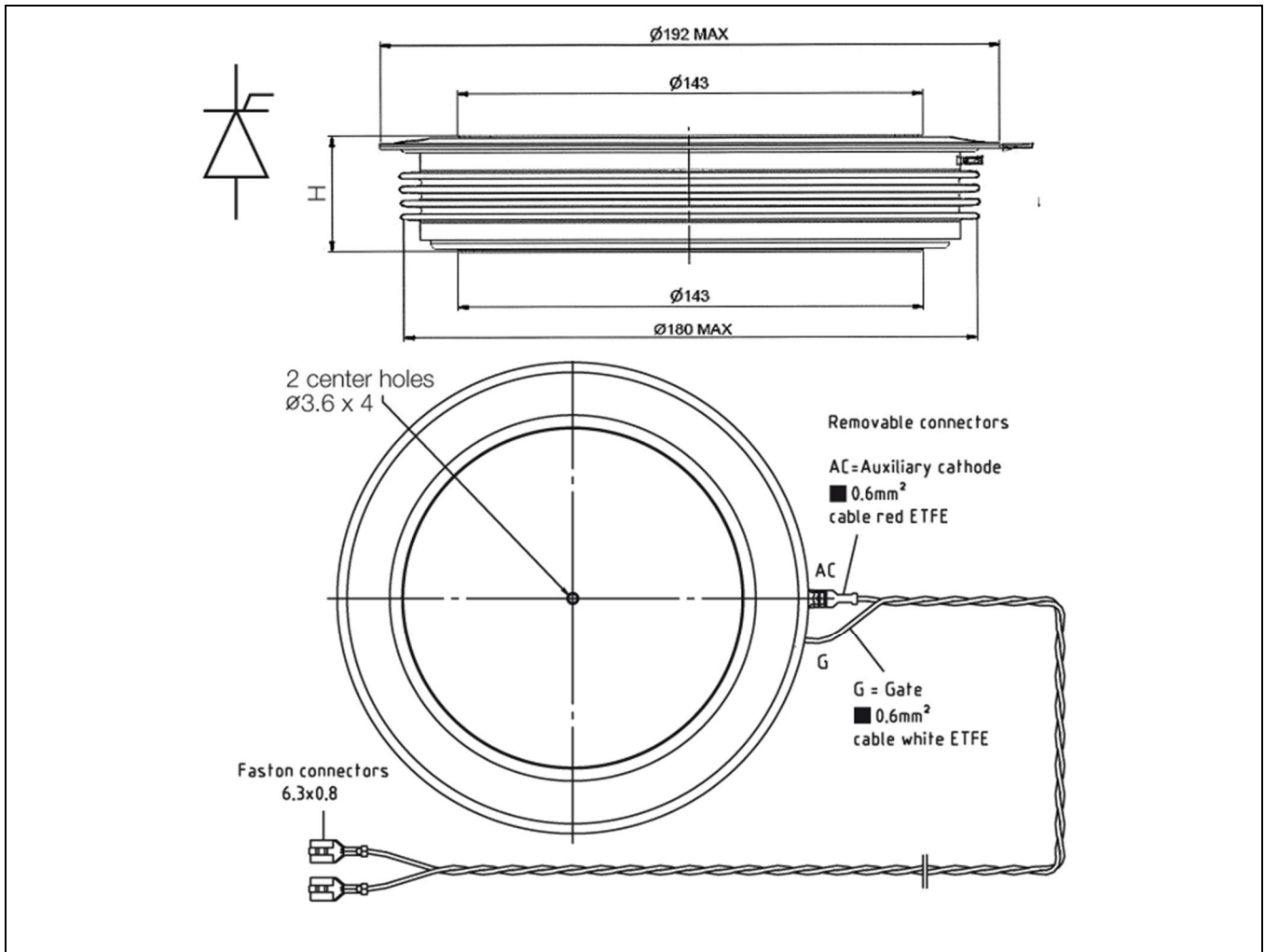


Fig. 14 Device Outline Drawing

Related documents:

5SYA 2020	Design of RC-Snubbers for Phase Control Applications
5SYA 2049	Voltage definitions for phase control and bi-directionally controlled thyristors
5SYA 2051	Voltage ratings of high power semiconductors
5SYA 2034	Gate-drive recommendations for phase control and bi-directionally controlled thyristors
5SYA 2036	Recommendations regarding mechanical clamping of Press-Pack High Power Semiconductors
5SYA 2102	Surge currents for Phase Control Thyristors
5SZK 9118	General Environmental Conditions for High Power Semiconductors

Please refer to <http://www.hitachiabb-powergrids.com/semiconductors> for current version of documents.

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